

**D** $T_C = 25$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$I_D@T_C=25$	10	A
	$I_D@T_C=75$	7.6	A
	$I_D@T_C=100$	6.3	A
Pulsed Drain Current	I_{DM}	25	A
Total Power Dissipation	$P_D@T_C=25$	70	W
Total Power Dissipation	$P_D@T_A=25$	2.5	W
Operating Junction Temperature	T_J	-55 to 150	
Storage Temperature			

Fig.1 Gate-Charge Characteristics

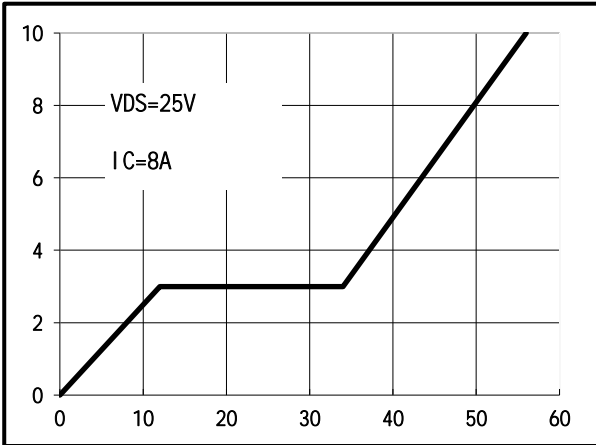


Fig.2 Capacitance Characteristics

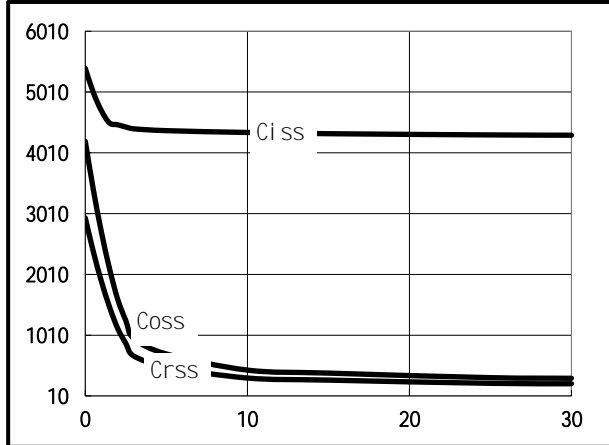


Fig.3 Power Dissipation

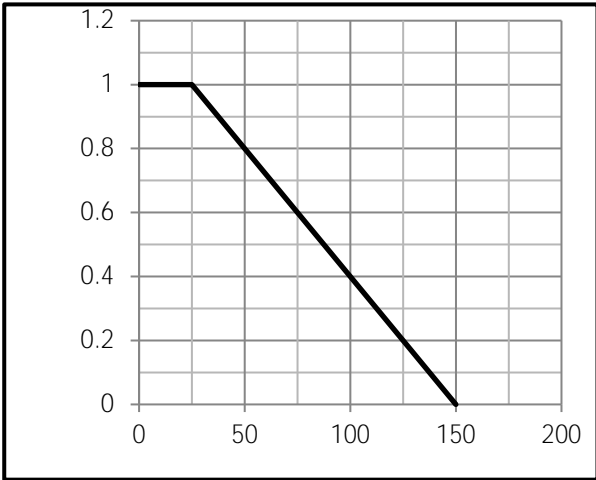


Fig.4 Typical output Characteristics

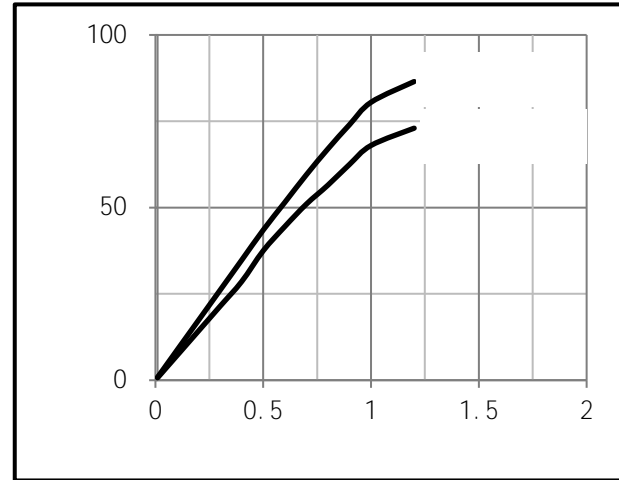


Fig.5 Threshold Voltage V.S Junction Temperature

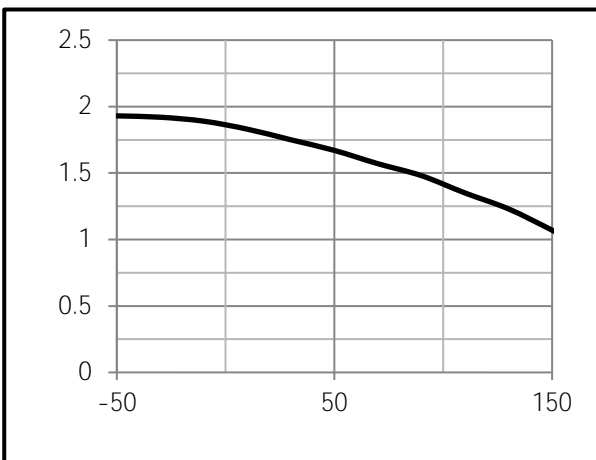
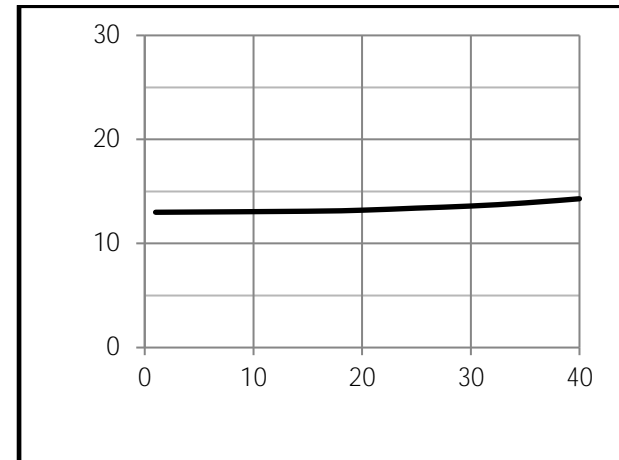


Fig.6 Resistance V.S Drain Current



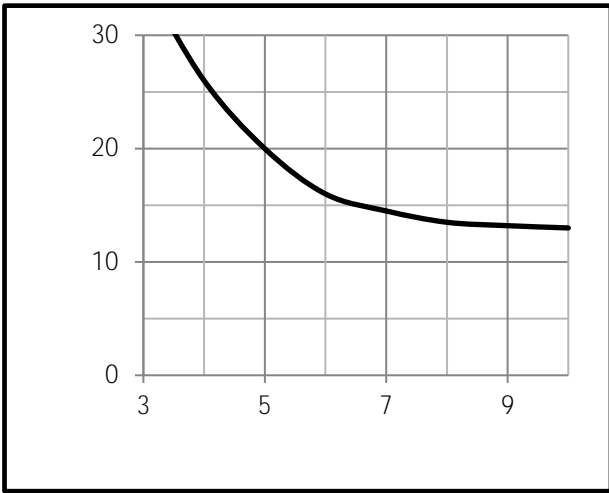


Fig.9 Switching Time Measurement Circuit

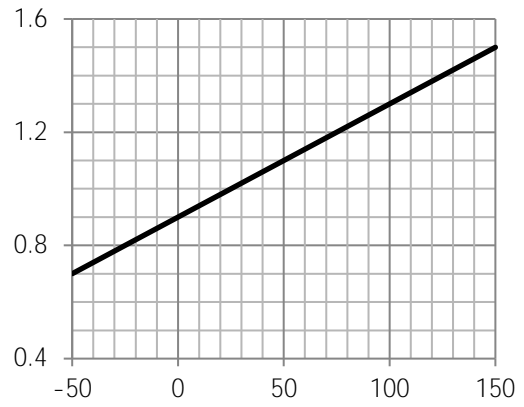


Fig.10 Gate Charge Waveform

Fig.11 Switching Time Measurement Circuit

Fig.12 Gate Charge Waveform

(SOP8)

Unit mm

SYMBOL	min	TYP	max	SYMBOL	min		max
A	4.80		5.00	C	1.30		1.50
A1	0.37		0.47	C1	0.55		0.75
A2		1.27		C2	0.55		0.65
A3		0.41		C3	0.05		0.20
B	5.80		6.20	C4	0.19	0.20	0.23
B1	3.80		4.00	D		1.05	
B2		5.00		D1	0.40		0.62

